

## Chip Specification

### General Description:

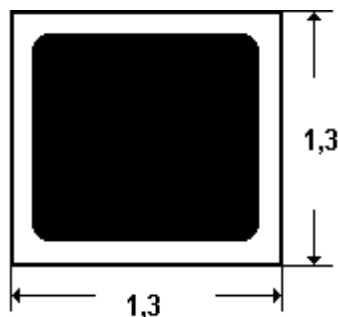
Schottky Diode chips with Mo-barrier for switch mode power rectifiers with the following features:

- \* **Guard-ring for stress protection**
- \* **Extremely low forward voltage**
- \* **125 °C operation junction temperature**
- \* **reverse avalanche behavior**

### Mechanical Data:

#### SB 1XX passivated Silicon Chip

Demension(mm)	1,3x1,3
Thickness:	350 +- 20 µm
Metallization:	
Top ( Anode ) :	Al Ag
Bottom ( Cathode ) :	TiNiAg



Forward Current(A)	1 A
Reverse Voltage (V):	23, 43, 100 V

Type	Chip	VR(V)	VF(V)@25 C	IRM@VRMM
	size(mm)		at If=1A	at 25 C
SB120	1,3x1,3	23 V	380mV	0,5mA
SB140	1,3x1,3	43 V	400mV	0,5mA
SB1100	1,3x1,3	100 V	650mV	0,5mA

Note: Other voltages, Vf & Top Metal AL are available

